

# Tim D Veal

## List of Publications by Citations

**Source:** <https://exaly.com/author-pdf/2686987/tim-d-veal-publications-by-citations.pdf>

**Version:** 2024-04-22

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

162  
papers

6,357  
citations

46  
h-index

73  
g-index

170  
ext. papers

7,000  
ext. citations

4.4  
avg, IF

5.47  
L-index

#	Paper	IF	Citations
162	Intrinsic electron accumulation at clean InN surfaces. <i>Physical Review Letters</i> , <b>2004</b> , 92, 036804	7.4	426
161	Band gap, electronic structure, and surface electron accumulation of cubic and rhombohedral In <sub>2</sub> O <sub>3</sub> . <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	323
160	Surface electron accumulation and the charge neutrality level in In <sub>2</sub> O <sub>3</sub> . <i>Physical Review Letters</i> , <b>2008</b> , 101, 116808	7.4	217
159	Electronic and optical properties of single crystal SnS <sub>2</sub> : an earth-abundant disulfide photocatalyst. <i>Journal of Materials Chemistry A</i> , <b>2016</b> , 4, 1312-1318	13	190
158	Origin of electron accumulation at wurtzite InN surfaces. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	189
157	Conductivity in transparent oxide semiconductors. <i>Journal of Physics Condensed Matter</i> , <b>2011</b> , 23, 334214.8	14.8	151
156	Bandgap and effective mass of epitaxial cadmium oxide. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 022101	3.4	140
155	Origin of the n-type conductivity of InN: The role of positively charged dislocations. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 252109	3.4	134
154	Band Alignments, Valence Bands, and Core Levels in the Tin Sulfides SnS, SnS <sub>2</sub> , and Sn <sub>2</sub> S <sub>3</sub> : Experiment and Theory. <i>Chemistry of Materials</i> , <b>2016</b> , 28, 3718-3726	9.6	123
153	InN/GaN valence band offset: High-resolution x-ray photoemission spectroscopy measurements. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	118
152	Shallow donor state of hydrogen in In <sub>2</sub> O <sub>3</sub> and SnO <sub>2</sub> : Implications for conductivity in transparent conducting oxides. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	116
151	Valence-band electronic structure of CdO, ZnO, and MgO from x-ray photoemission spectroscopy and quasi-particle-corrected density-functional theory calculations. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	106
150	Growth, disorder, and physical properties of ZnSnN <sub>2</sub> . <i>Applied Physics Letters</i> , <b>2013</b> , 103, 042109	3.4	98
149	Bulk transport measurements in ZnO: The effect of surface electron layers. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	97
148	Determination of the branch-point energy of InN: Chemical trends in common-cation and common-anion semiconductors. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	96
147	Universality of electron accumulation at wurtzite c- and a-plane and zinc-blende InN surfaces. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 092101	3.4	96
146	Quantized electron accumulation states in indium nitride studied by angle-resolved photoemission spectroscopy. <i>Physical Review Letters</i> , <b>2006</b> , 97, 237601	7.4	91

145	Valence band offset of InN/AlN heterojunctions measured by x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 132105	3.4	81
144	Surface band-gap narrowing in quantized electron accumulation layers. <i>Physical Review Letters</i> , <b>2010</b> , 104, 256803	7.4	80
143	Growth and properties of GaSbBi alloys. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 142106	3.4	78
142	Transition from electron accumulation to depletion at InGaN surfaces. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 202110	3.4	76
141	Band Gap Dependence on Cation Disorder in ZnSnN <sub>2</sub> Solar Absorber. <i>Advanced Energy Materials</i> , <b>2015</b> , 5, 1501462	21.8	75
140	Observation of quantized subband states and evidence for surface electron accumulation in CdO from angle-resolved photoemission spectroscopy. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	70
139	Unification of the electrical behavior of defects, impurities, and surface states in semiconductors: Virtual gap states in CdO. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	69
138	Valence band offset of the ZnO/AlN heterojunction determined by x-ray photoemission spectroscopy. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 202108	3.4	69
137	Nonparabolic coupled Poisson-Schrödinger solutions for quantized electron accumulation layers: Band bending, charge profile, and subbands at InN surfaces. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	67
136	In adlayers on c-plane InN surfaces: A polarity-dependent study by x-ray photoemission spectroscopy. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	64
135	Origin of High Mobility in Molybdenum-Doped Indium Oxide. <i>Chemistry of Materials</i> , <b>2015</b> , 27, 2788-2796	9.6	61
134	Observation of shallow-donor muonium in Ga <sub>2</sub> O <sub>3</sub> : Evidence for hydrogen-induced conductivity. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 062110	3.4	61
133	High Bi content GaSbBi alloys. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 043511	2.5	60
132	Polarity effects in the x-ray photoemission of ZnO and other wurtzite semiconductors. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 101906	3.4	60
131	Electron depletion at InAs free surfaces: Doping-induced acceptorlike gap states. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	59
130	Self-Compensation in Transparent Conducting F-Doped SnO <sub>2</sub> . <i>Advanced Functional Materials</i> , <b>2018</b> , 28, 1701900	15.6	56
129	Temperature dependence of the direct bandgap and transport properties of CdO. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 022102	3.4	55
128	Valence-band structure of InN from x-ray photoemission spectroscopy. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	55

127	Variation of band bending at the surface of Mg-doped InGaN: Evidence of p-type conductivity across the composition range. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	53
126	Sb-induced phase control of InAsSb nanowires grown by molecular beam epitaxy. <i>Nano Letters</i> , <b>2015</b> , 15, 1109-16	11.5	52
125	Surface Structure and Electronic Properties of In <sub>2</sub> O <sub>3</sub> (111) Single-Crystal Thin Films Grown on Y-Stabilized ZrO <sub>2</sub> (111). <i>Chemistry of Materials</i> , <b>2009</b> , 21, 4353-4355	9.6	51
124	Valence-band density of states and surface electron accumulation in epitaxial SnO <sub>2</sub> films. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	50
123	Band anticrossing in GaN <sub>x</sub> Sb <sub>1-x</sub> . <i>Applied Physics Letters</i> , <b>2006</b> , 89, 111921	3.4	49
122	Surfactant effect of antimony addition to the morphology of self-catalyzed InAs <sub>1-x</sub> Sb <sub>x</sub> nanowires. <i>Nano Research</i> , <b>2015</b> , 8, 1309-1319	10	48
121	Negative band gaps in dilute InN <sub>x</sub> Sb <sub>1-x</sub> alloys. <i>Physical Review Letters</i> , <b>2004</b> , 92, 136801	7.4	47
120	Photoluminescence spectroscopy of bandgap reduction in dilute InNAs alloys. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 182114	3.4	47
119	Clean wurtzite InN surfaces prepared with atomic hydrogen. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2005</b> , 23, 617-620	2.9	47
118	Theoretical and experimental studies of electronic band structure for GaSb <sub>1-x</sub> Bi <sub>x</sub> in the dilute Bi regime. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 355107	3	46
117	Direct Measurements of Fermi Level Pinning at the Surface of Intrinsically n-Type InGaAs Nanowires. <i>Nano Letters</i> , <b>2016</b> , 16, 5135-42	11.5	46
116	Electron mobility in CdO films. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 073712	2.5	45
115	Band gap temperature-dependence of close-space sublimation grown Sb <sub>2</sub> Se <sub>3</sub> by photo-reflectance. <i>APL Materials</i> , <b>2018</b> , 6, 084901	5.7	45
114	Band gap reduction in GaNSb alloys due to the anion mismatch. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 132101	3.4	44
113	Ge interface engineering using ultra-thin La <sub>2</sub> O <sub>3</sub> and Y <sub>2</sub> O <sub>3</sub> films: A study into the effect of deposition temperature. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 114102	2.5	41
112	Temperature dependence of the band gap of GaSb <sub>1-x</sub> Bi <sub>x</sub> alloys with 0 . <i>Applied Physics Letters</i> , <b>2013</b> , 103, 261907	3.4	40
111	Core Levels, Band Alignments, and Valence-Band States in CuSbS for Solar Cell Applications. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 41916-41926	9.5	40
110	Bi-induced band gap reduction in epitaxial InSbBi alloys. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 212101	3.4	38

109	Thickness dependence of the strain, band gap and transport properties of epitaxial In <sub>2</sub> O <sub>3</sub> thin films grown on Y-stabilised ZrO <sub>2</sub> (111). <i>Journal of Physics Condensed Matter</i> , <b>2011</b> , 23, 334211	1.8	38
108	The influence of Sn doping on the growth of In <sub>2</sub> O <sub>3</sub> on Y-stabilized ZrO <sub>2</sub> (100) by oxygen plasma assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 013703	2.5	38
107	Temperature invariance of InN electron accumulation. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	38
106	Transition from electron accumulation to depletion at InGa <sub>2</sub> O <sub>3</sub> surfaces: The role of hydrogen and the charge neutrality level. <i>APL Materials</i> , <b>2019</b> , 7, 022528	5.7	38
105	Valence band density of states of zinc-blende and wurtzite InN from x-ray photoemission spectroscopy and first-principles calculations. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	37
104	Indium nitride: Evidence of electron accumulation. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2004</b> , 22, 2175		37
103	Realization of Vertically Aligned, Ultrahigh Aspect Ratio InAsSb Nanowires on Graphite. <i>Nano Letters</i> , <b>2015</b> , 15, 4348-55	11.5	35
102	Unintentional conductivity of indium nitride: transport modelling and microscopic origins. <i>Journal of Physics Condensed Matter</i> , <b>2009</b> , 21, 174201	1.8	35
101	Isotype Heterojunction Solar Cells Using n-Type Sb <sub>2</sub> Se <sub>3</sub> Thin Films. <i>Chemistry of Materials</i> , <b>2020</b> , 32, 2621-2630	1.8	34
100	Contactless electroreflectance and theoretical studies of band gap and spin-orbit splitting in In <sub>1-x</sub> Bi <sub>x</sub> dilute bismide with x=0.034. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 222104	3.4	34
99	Inversion and accumulation layers at InN surfaces. <i>Journal of Crystal Growth</i> , <b>2006</b> , 288, 268-272	1.6	33
98	Band bending at the surfaces of In-rich InGaN alloys. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 113716	2.5	32
97	Resonant doping for high mobility transparent conductors: the case of Mo-doped In <sub>2</sub> O <sub>3</sub> . <i>Materials Horizons</i> , <b>2020</b> , 7, 236-243	14.4	30
96	The influence of conduction band plasmons on core-level photoemission spectra of InN. <i>Surface Science</i> , <b>2008</b> , 602, 871-875	1.8	29
95	Photoluminescence of InNAs alloys: S-shaped temperature dependence and conduction-band nonparabolicity. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	29
94	Resonant Ta Doping for Enhanced Mobility in Transparent Conducting SnO. <i>Chemistry of Materials</i> , <b>2020</b> , 32, 1964-1973	9.6	28
93	Growth of dilute GaNSb by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , <b>2005</b> , 278, 188-192	1.6	28
92	Atypically small temperature-dependence of the direct band gap in the metastable semiconductor copper nitride Cu <sub>3</sub> N. <i>Physical Review B</i> , <b>2017</b> , 95,	3.3	27

91	Low- and high-energy photoluminescence from GaSb <sub>1-x</sub> Bi <sub>x</sub> with 0 ≤ x ≤ 1. <i>Applied Physics Express</i> , <b>2014</b> , 7, 1112024	2.4	27
90	Core-level photoemission spectroscopy of nitrogen bonding in GaN <sub>x</sub> As <sub>1-x</sub> alloys. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 1550-1552	3.4	27
89	Vacancy-Ordered Double Perovskite CsTeI Thin Films for Optoelectronics. <i>Chemistry of Materials</i> , <b>2020</b> , 32, 6676-6684	9.6	26
88	Surface, bulk, and interface electronic properties of nonpolar InN. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 112103	3.3	26
87	Growth of ZnSnN <sub>2</sub> by Molecular Beam Epitaxy. <i>Journal of Electronic Materials</i> , <b>2014</b> , 43, 884-888	1.9	25
86	Passivation and reconstruction-dependent electron accumulation at sulphur treated InAs() surfaces. <i>Surface Science</i> , <b>2003</b> , 523, 179-188	1.8	25
85	Profiling of electron accumulation layers in the near-surface region of InAs (110). <i>Physical Review B</i> , <b>2001</b> , 64,	3.3	25
84	Identifying Raman modes of Sb <sub>2</sub> Se <sub>3</sub> and their symmetries using angle-resolved polarised Raman spectra. <i>Journal of Materials Chemistry A</i> , <b>2020</b> , 8, 8337-8344	13	25
83	Valence band modification of Cr <sub>2</sub> O <sub>3</sub> by Ni-doping: creating a high figure of merit p-type TCO. <i>Journal of Materials Chemistry C</i> , <b>2017</b> , 5, 12610-12618	7.1	24
82	Bi flux-dependent MBE growth of GaSbBi alloys. <i>Journal of Crystal Growth</i> , <b>2015</b> , 425, 241-244	1.6	24
81	Band Alignments, Band Gap, Core Levels, and Valence Band States in CuBiS for Photovoltaics. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 27033-27047	9.5	22
80	Ab-Initio Studies of Electronic and Spectroscopic Properties of MgO, ZnO and CdO. <i>Journal of the Korean Physical Society</i> , <b>2008</b> , 53, 2811-2815	0.6	22
79	Sulphur-induced electron accumulation on InAs: a comparison of the (001) and (111)B surfaces. <i>Surface Science</i> , <b>2003</b> , 544, 320-328	1.8	21
78	Influence of Polymorphism on the Electronic Structure of Ga <sub>2</sub> O <sub>3</sub> . <i>Chemistry of Materials</i> , <b>2020</b> , 32, 8460-8470	9.6	21
77	Optical absorption by dilute GaNSb alloys: Influence of N pair states. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 042110	3.4	20
76	GeSe: Optical Spectroscopy and Theoretical Study of a van der Waals Solar Absorber. <i>Chemistry of Materials</i> , <b>2020</b> , 32, 3245-3253	9.6	19
75	HREELS and photoemission study of GaSb()--(111)B surfaces prepared by optimal atomic hydrogen cleaning. <i>Surface Science</i> , <b>2002</b> , 499, 251-260	1.8	19
74	Giant reduction of InN surface electron accumulation: compensation of surface donors by Mg dopants. <i>Physical Review Letters</i> , <b>2012</b> , 109, 247605	7.4	18

73	N incorporation in GaInNSb alloys and lattice matching to GaSb. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 033502	2.5	18
72	X-ray photoemission spectroscopy determination of the InN/yttria stabilized cubic-zirconia valence band offset. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 112103	3.4	18
71	Electron accumulation at InN/AlN and InN/GaN interfaces. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 2246-2249		18
70	The first 25 years of semiconductor muonics at ISIS, modelling the electrical activity of hydrogen in inorganic semiconductors and high- $\epsilon$ dielectrics. <i>Physica Scripta</i> , <b>2013</b> , 88, 068503	2.6	17
69	Controlled nitrogen incorporation in GaNSb alloys. <i>AIP Advances</i> , <b>2011</b> , 1, 032159	1.5	17
68	Surface electronic properties of undoped InAlN alloys. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 172105	3.4	17
67	Surface electronic properties of clean and S-terminated InSb(001) and (111)B. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 083709	2.5	17
66	X-ray photoemission studies of the electronic structure of single-crystalline CdO(100). <i>Superlattices and Microstructures</i> , <b>2007</b> , 42, 197-200	2.8	17
65	Effect of hydrogen in dilute In <sub>x</sub> Sb <sub>1-x</sub> alloys grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1776-1778	3.4	17
64	Controlled oxide removal for the preparation of damage-free InAs(110) surfaces. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 1665-1667	3.4	17
63	Surface electronic properties of n- and p-type InGaN alloys. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 881-883	1.3	16
62	Scanning tunnelling spectroscopy of quantized electron accumulation at In <sub>x</sub> Ga <sub>1-x</sub> N surfaces. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2006</b> , 203, 85-92	1.6	16
61	Sulfur passivation of InN surface electron accumulation. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 192111	3.4	15
60	Influence of growth conditions and polarity on interface-related electron density in InN. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 103703	2.5	15
59	Growth and characterisation of high quality MBE grown In <sub>x</sub> Sb <sub>1-x</sub> . <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2007</b> , 1, 104-106	2.5	13
58	Dilute antimonide nitrides for very long wavelength infrared applications <b>2006</b> , 6206, 201		13
57	Indium Gallium Oxide Alloys: Electronic Structure, Optical Gap, Surface Space Charge, and Chemical Trends within Common-Cation Semiconductors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 2807-2819	2.5	13
56	Optimization of self-catalyzed InAs Nanowires on flexible graphite for photovoltaic infrared photodetectors. <i>Scientific Reports</i> , <b>2017</b> , 7, 46110	4.9	12



55	Band gap temperature-dependence and exciton-like state in copper antimony sulphide, CuSbS <sub>2</sub> . <i>APL Materials</i> , <b>2018</b> , 6, 084904	5.7	12
54	N incorporation and associated localized vibrational modes in GaSb. <i>Physical Review B</i> , <b>2014</b> , 89,	3.3	12
53	Influence of charged-dislocation density variations on carrier mobility in heteroepitaxial semiconductors: The case of SnO <sub>2</sub> on sapphire. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	12
52	In-adlayers on non-polar and polar InN surfaces: Ion scattering and photoemission studies. <i>Physica B: Condensed Matter</i> , <b>2007</b> , 401-402, 351-354	2.8	12
51	Graphitic platform for self-catalysed InAs nanowires growth by molecular beam epitaxy. <i>Nanoscale Research Letters</i> , <b>2014</b> , 9, 321	5	11
50	ZnSnN <sub>2</sub> : A new earth-abundant element semiconductor for solar cells <b>2012</b> ,		11
49	In-vacancies in Si-doped InN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 1083-1086		11
48	Hole density and acceptor-type defects in MBE-grown GaSb <sub>1-x</sub> Bix. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 295102	3	10
47	Photoreflectance spectroscopy of GaInSbBi and AlGaSbBi quaternary alloys. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 112102	3.4	10
46	Self-compensation in highly n-type InN. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 011903	3.4	10
45	Low-energy nitrogen ion implantation of InSb. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 4935-4938	2.5	10
44	Photoelectron spectroscopy study of Ga <sub>1-x</sub> MnxAs(0 0 1) surface oxide and low temperature cleaning. <i>Surface Science</i> , <b>2005</b> , 585, 66-74	1.8	10
43	Evidence of a second-order Peierls-driven metal-insulator transition in crystalline NbO <sub>2</sub> . <i>Physical Review Materials</i> , <b>2019</b> , 3,	3.2	10
42	Molecular-beam epitaxy and lattice parameter of Ga <sub>x</sub> Sb <sub>1-x</sub> : deviation from Vegard's law for x > 0.02. <i>Journal Physics D: Applied Physics</i> , <b>2013</b> , 46, 264003	3	9
41	Extreme band bending at MBE-grown InAs(001) surfaces induced by in situ sulphur passivation. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 196-200	1.6	9
40	Band gap reduction in In <sub>x</sub> Sb <sub>1-x</sub> alloys: Optical absorption, k · P modeling, and density functional theory. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 132104	3.4	9
39	Intrinsic point defects and the n- and p-type dopability of the narrow gap semiconductors GaSb and InSb. <i>Physical Review B</i> , <b>2019</b> , 100,	3.3	8
38	Growth of dilute nitride alloys of GaInSb lattice-matched to GaSb. <i>Journal of Crystal Growth</i> , <b>2007</b> , 304, 338-341	1.6	8



37	How Oxygen Exposure Improves the Back Contact and Performance of Antimony Selenide Solar Cells. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 52595-52602	9.5	8
36	Natural Band Alignments and Band Offsets of Sb <sub>2</sub> Se <sub>3</sub> Solar Cells. <i>ACS Applied Energy Materials</i> , <b>2020</b> , 3, 11617-11626	6.1	7
35	Chemical etching of Sb <sub>2</sub> Se <sub>3</sub> solar cells: surface chemistry and back contact behaviour. <i>JPhys Energy</i> , <b>2019</b> , 1, 045001	4.9	7
34	Indium-incorporation enhancement of photoluminescence properties of Ga(In)SbBi alloys. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 375102	3	7
33	Electron spectroscopy of dilute nitrides. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, S3201-S3214	1.8	7
32	Electron dynamics in In <sub>N</sub> Sb <sub>1-x</sub> . <i>Applied Physics Letters</i> , <b>2003</b> , 83, 2169-2171	3.4	7
31	Increased p-type conductivity in Ga <sub>N</sub> Sb <sub>1-x</sub> , experimental and theoretical aspects. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 085708	2.5	6
30	Sb 5s <sub>2</sub> lone pairs and band alignment of Sb <sub>2</sub> Se <sub>3</sub> : a photoemission and density functional theory study. <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 12615-12622	7.1	6
29	Structural, electrical and optical characterization of MOCVD grown In-rich InGaN layers. <i>Journal of Crystal Growth</i> , <b>2012</b> , 358, 51-56	1.6	5
28	MBE growth and characterization of Mn-doped InN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2012</b> , 30, 02B124	1.3	5
27	Na <sub>2</sub> Fe <sub>2</sub> O <sub>5</sub> S <sub>2</sub> , a new earth abundant oxysulphide cathode material for Na-ion batteries. <i>Journal of Materials Chemistry A</i> , <b>2020</b> , 8, 20553-20569	13	5
26	Growth and Characterization of Sb <sub>2</sub> Se <sub>3</sub> Single Crystals for Fundamental Studies <b>2018</b> ,		5
25	Electronic Properties of Post-transition Metal Oxide Semiconductor Surfaces. <i>Springer Series in Materials Science</i> , <b>2012</b> , 127-145	0.9	4
24	Surface electronic properties of In-rich InGaN alloys grown by MOCVD. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 662-665		4
23	Impact of degeneraten-doping on the optical absorption edge in transparent conducting cadmium oxide <b>2013</b> ,		4
22	Stable passivation of InN surface electron accumulation with sulphur treatment. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 1605-1607		4
21	Doping-dependence of subband energies in quantized electron accumulation at InN surfaces. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2007</b> , 204, 536-542	1.6	4
20	InN: Fermi level stabilization by low-energy ion bombardment. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 1841-1845		4

19	InN{0001} polarity by ion scattering spectroscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 2301-2304		4
18	Sn 5s <sup>2</sup> lone pairs and the electronic structure of tin sulphides: A photorefectance, high-energy photoemission, and theoretical investigation. <i>Physical Review Materials</i> , <b>2020</b> , 4,	3.2	4
17	Sulfur passivation of surface electrons in highly Mg-doped InN. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 103702	2.5	3
16	Growth and characterisation of dilute antimonide nitride materials for long-wavelength applications. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 399-402	1.8	3
15	Dielectric function of degenerate InSb: Beyond the hydrodynamic model. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	3
14	Temperature-dependent two-dimensional plasmons at clean and hydrogenated Ge(001) surfaces. <i>Physical Review B</i> , <b>2000</b> , 62, 7330-7335	3.3	3
13	Influence of annealing on the electrical characteristic of GaSbBi Schottky diodes. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 053103	2.5	2
12	Surface electronic properties of Mg-doped InAlN alloys. <i>Physica Status Solidi (B): Basic Research</i> , <b>2009</b> , 246, 1169-1172	1.3	2
11	Determination of the substitutional nitrogen content and the electron effective mass in InN <sub>x</sub> Sb <sub>1-x</sub> (001) epitaxial layers. <i>IEE Proceedings: Optoelectronics</i> , <b>2003</b> , 150, 102		2
10	Plasmon damping in molecular beam epitaxial-grown InAs(100). <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2002</b> , 20, 1766		2
9	Band alignment of Sb <sub>2</sub> O <sub>3</sub> and Sb <sub>2</sub> Se <sub>3</sub> . <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 235301	2.5	2
8	Epitaxial InGaN on nitridated Si(111) for photovoltaic applications <b>2012</b> ,		1
7	The donor nature of muonium in undoped, heavily n-type and p-type InAs. <i>Journal of Physics Condensed Matter</i> , <b>2009</b> , 21, 075803	1.8	1
6	Response to Comment on Bandgap and effective mass determination of epitaxial cadmium oxide[Appl. Phys. Lett. 92, 106103 (2008)]. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 106104	3.4	1
5	Fuchs&liower phonon excitations in GaNAs alloys. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 8466-8468	2.5	1
4	Accelerating the development of new solar absorbers by photoemission characterization coupled with density functional theory. <i>JPhys Energy</i> , <b>2021</b> , 3, 032001	4.9	1
3	Nitrogen pair-induced temperature insensitivity of the band gap of GaNSb alloys. <i>Journal Physics D: Applied Physics</i> , <b>2019</b> , 52, 045105		3
2	Band offsets of metal oxide contacts on TlBr radiation detectors. <i>Journal of Applied Physics</i> , <b>2021</b> , 130, 175305	2.5	

- 1 Growth and Characterisation of Dilute Antimonide Nitride Materials for Long Wavelength Applications. *Springer Proceedings in Physics*, **2008**, 49-51 0.2